

MBRJ2045CTG

Product Preview SWITCHMODE Power Rectifier

Features and Benefits

- Low Forward Voltage
- Low Power Loss / High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 20 A Total (10 A Per Diode Leg)
- This is a Pb-Free Device

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B
Machine Model = C

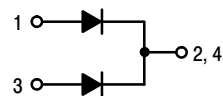
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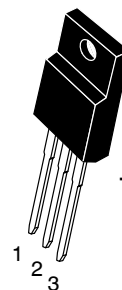
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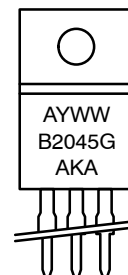
SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 45 VOLTS



MARKING DIAGRAM



TO-220 FULLPAK™
CASE 221AH
CT SUFFIX



| | |
|-----|---------------------|
| A | = Assembly Location |
| Y | = Year |
| WW | = Work Week |
| G | = Pb-Free Package |
| AKA | = Diode Polarity |

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|---------------------------------|-------------|------------------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 45 | V |
| Average Rectified Forward Current Per Device Per Diode ($T_C = 165^\circ\text{C}$) | $I_{F(AV)}$ | 20 10 | A |
| Peak Repetitive Forward Current per Diode Leg (Square Wave, 20 kHz, $T_C = 163^\circ\text{C}$) | I_{FRM} | 20 | A |
| Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz) | I_{FSM} | 150 | A |
| Peak Repetitive Reverse Surge Current (2.0 μs , 1.0 kHz) See Figure 11 | I_{RRM} | 1.0 | A |
| Storage Temperature Range | T_{stg} | -65 to +175 | $^\circ\text{C}$ |
| Operating Junction Temperature (Note 1) | T_J | -65 to +175 | $^\circ\text{C}$ |
| Voltage Rate of Change (Rated V_R) | dv/dt | 10,000 | V/ μs |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|------------------------------------|------------|---------------------------|
| Maximum Thermal Resistance - Junction-to-Case - Junction-to-Ambient | $R_{\theta JC}$ $R_{\theta JA}$ | 4.3 105 | $^\circ\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|--------|-----|----------------------|----------------------|------|
| Instantaneous Forward Voltage (Note 2) ($i_F = 10$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 20$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 20$ Amps, $T_J = 25^\circ\text{C}$) | V_F | - | 0.50 0.67 0.71 | 0.57 0.72 0.84 | V |
| Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 125^\circ\text{C}$) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) | i_R | - | 10.4 0.02 | 15 0.1 | mA |

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

DEVICE ORDERING INFORMATION

| Device Order Number | Package Type | Shipping [†] |
|---------------------|-----------------------|-----------------------|
| MBRJ2045CTG | TO-220FP (Pb-Free) | 50 Units / Rail |

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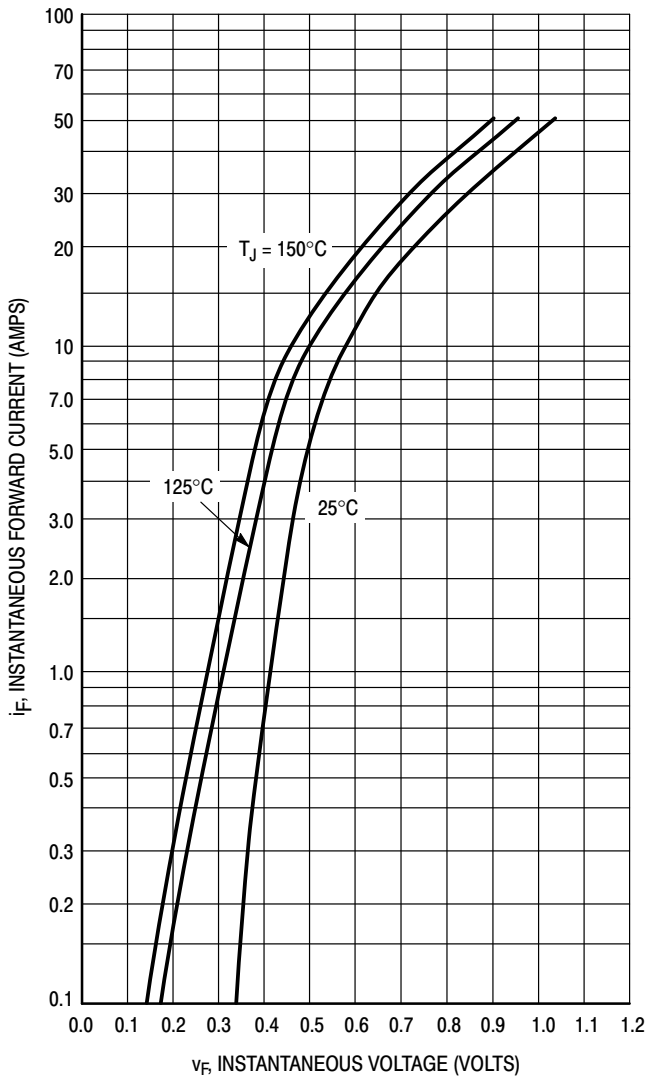


Figure 1. Typical Forward Voltage

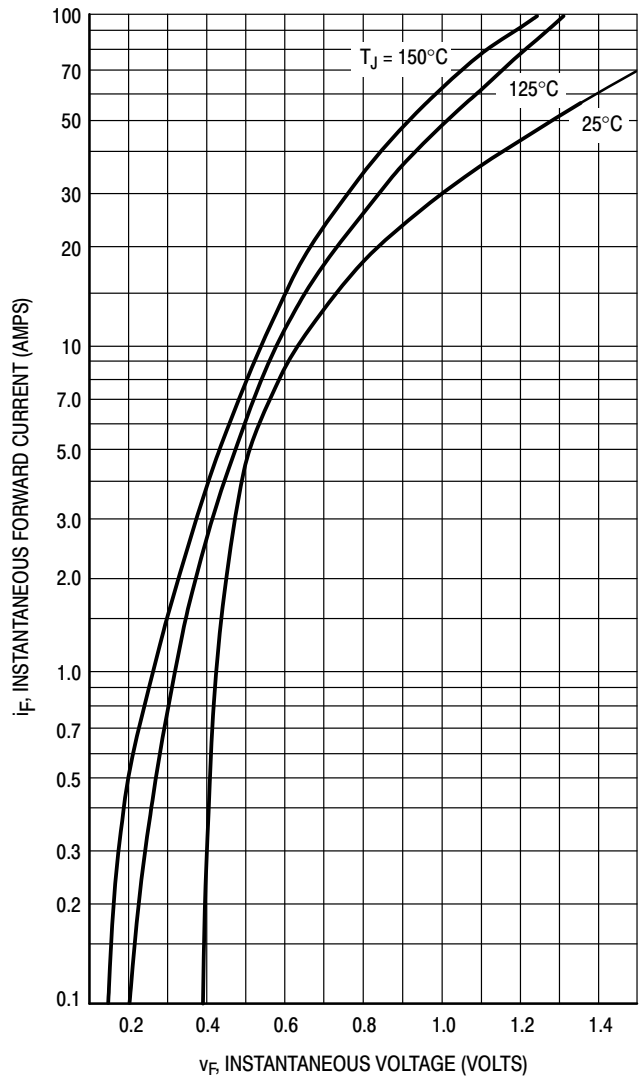


Figure 2. Maximum Forward Voltage

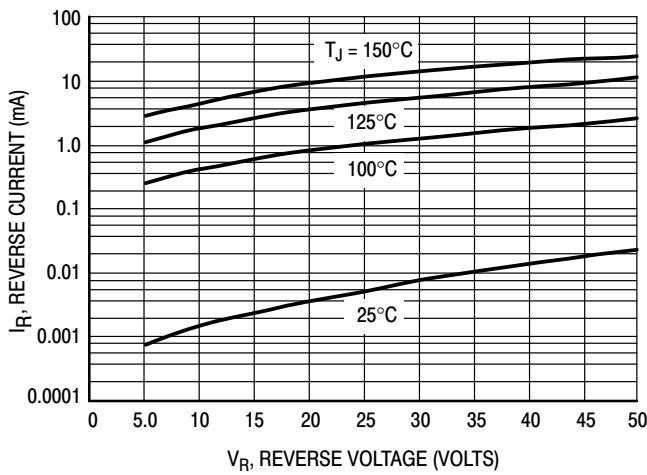


Figure 3. Typical Reverse Current

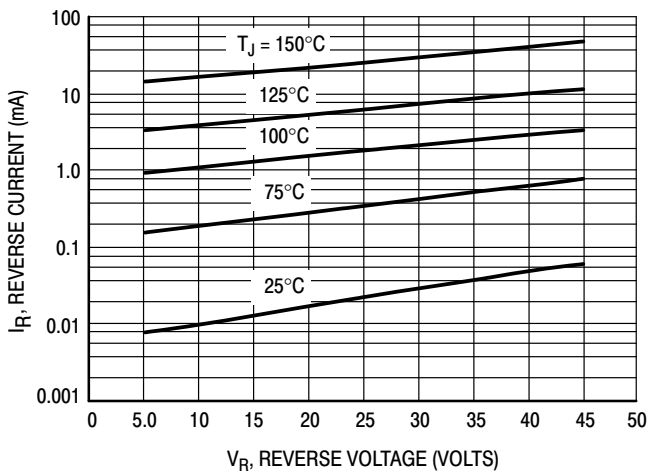


Figure 4. Maximum Reverse Current

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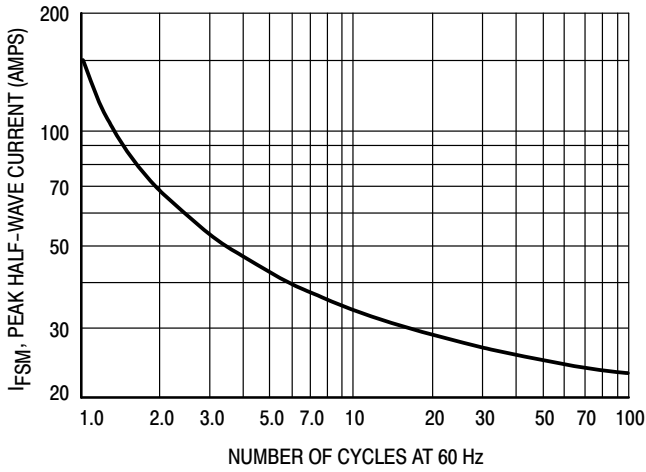


Figure 5. Maximum Surge Capability

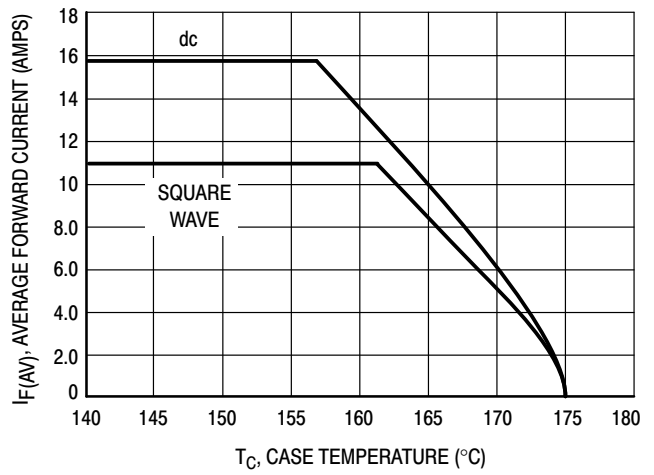


Figure 6. Current Derating, Case, Per Leg

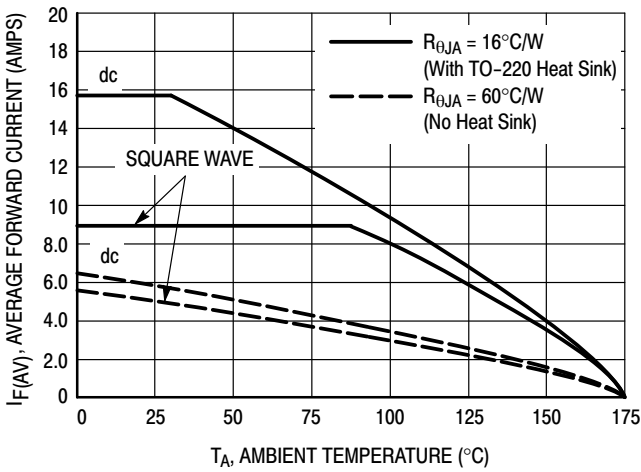


Figure 7. Current Derating, Ambient, Per Leg

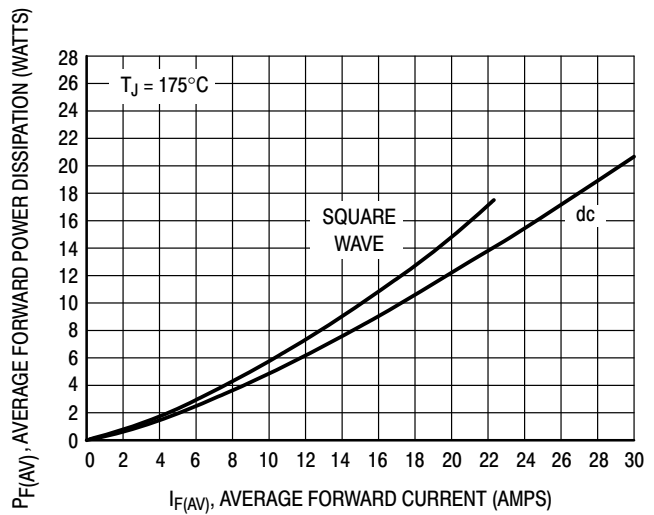


Figure 8. Forward Power Dissipation

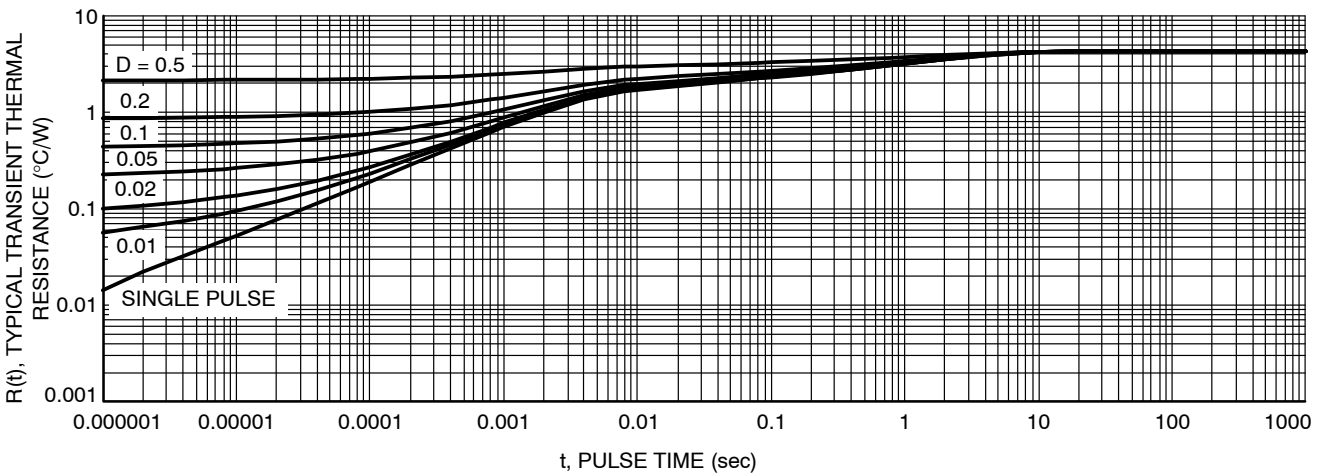


Figure 9. Typical Transient Thermal Response, Junction-to-Case

HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 10.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 percent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

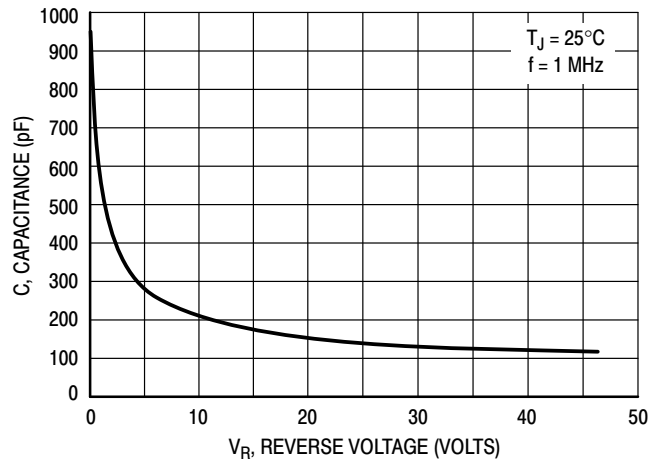


Figure 10. Typical Capacitance

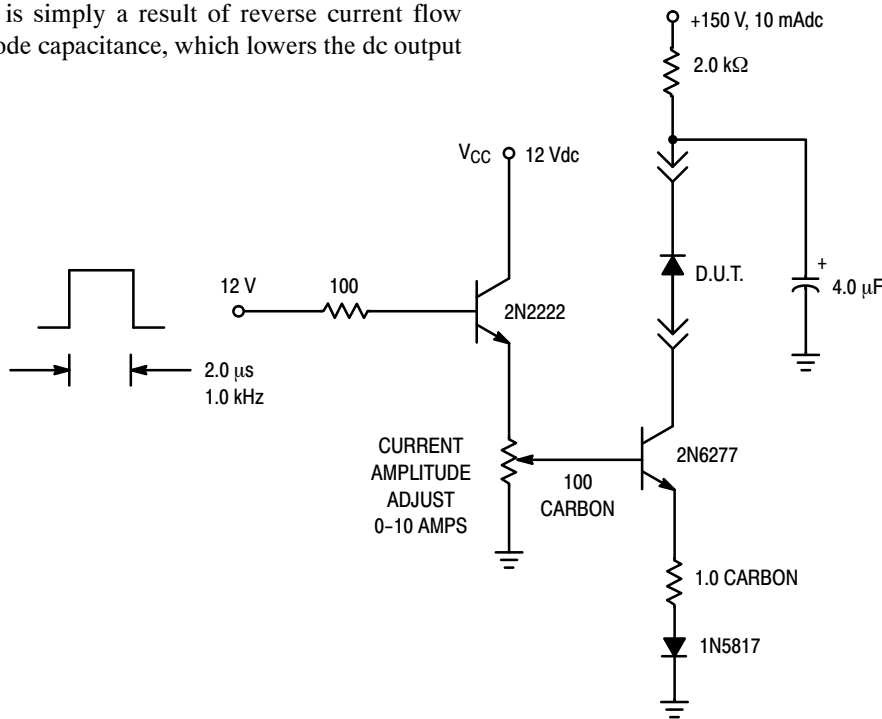
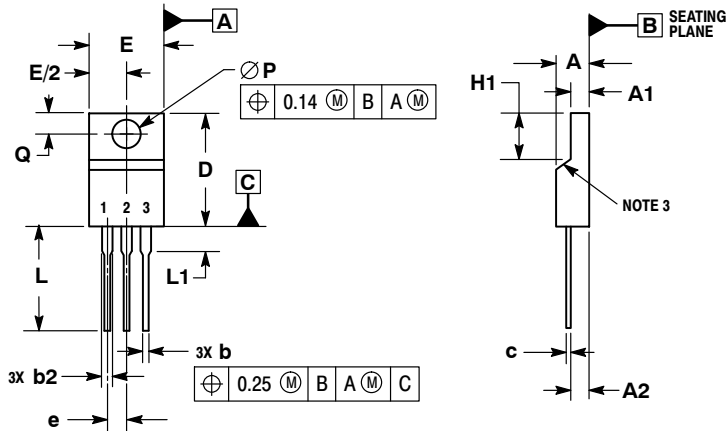


Figure 11. Test Circuit for dv/dt and Reverse Surge Current

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PACKAGE DIMENSIONS

TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

| DIM | MILLIMETERS | |
|-----|-------------|-------|
| | MIN | MAX |
| A | 4.30 | 4.70 |
| A1 | 2.50 | 2.90 |
| A2 | 2.50 | 2.70 |
| b | 0.54 | 0.84 |
| b2 | 1.10 | 1.40 |
| c | 0.49 | 0.79 |
| D | 14.70 | 15.30 |
| E | 9.70 | 10.30 |
| e | 2.54 BSC | |
| H1 | 6.70 | 7.10 |
| L | 12.70 | 14.73 |
| L1 | --- | 2.80 |
| P | 3.00 | 3.40 |
| Q | 2.80 | 3.20 |

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